

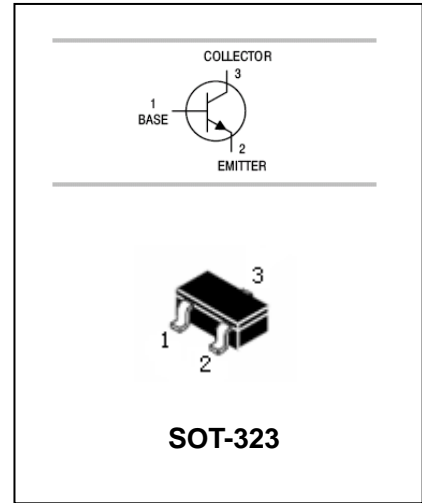


## NPN Silicon Epitaxial Planar Transistor

## KTC4076

### FEATURES

- Excellent  $H_{FE}$  Linearity.
- Complementary to KTA2015
- Power dissipation. ( $P_C=100mW$ )



### APPLICATIONS

- General purpose and switching application.

### ORDERING INFORMATION

Type No.	Marking	Package Code
KTC4076	WOWY	SOT-323

### MAXIMUM RATING @ $T_a=25^{\circ}C$ unless otherwise specified

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	35	V
$V_{CEO}$	Collector-Emitter Voltage	30	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current -Continuous	500	mA
$P_C$	Collector Dissipation	100	mW
$T_j, T_{stg}$	Junction and Storage Temperature	-55 to +150	$^{\circ}C$



**NPN Silicon Epitaxial Planar Transistor**

**KTC4076**

**ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified**

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=35V, I_E=0$			0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=5V, I_C=0$			0.1	$\mu A$
DC current gain	$h_{FE}$	$V_{CE}=1V, I_C=100mA$	70		240	
		$V_{CE}=6V, I_C=400mA$	25			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=100mA, I_B=10mA$		0.1	0.25	V
Transition frequency	$f_T$	$V_{CE}=6V, I_C=20mA$				MHz
Collector output capacitance	$C_{ob}$	$V_{CB}=6V, I_E=0mA$ $f=1MHz$		7.0		pF

**CLASSIFICATION OF  $h_{FE(1)}$**

Range	O	Y
Range	70-140	120-240
Marking	WO	WY

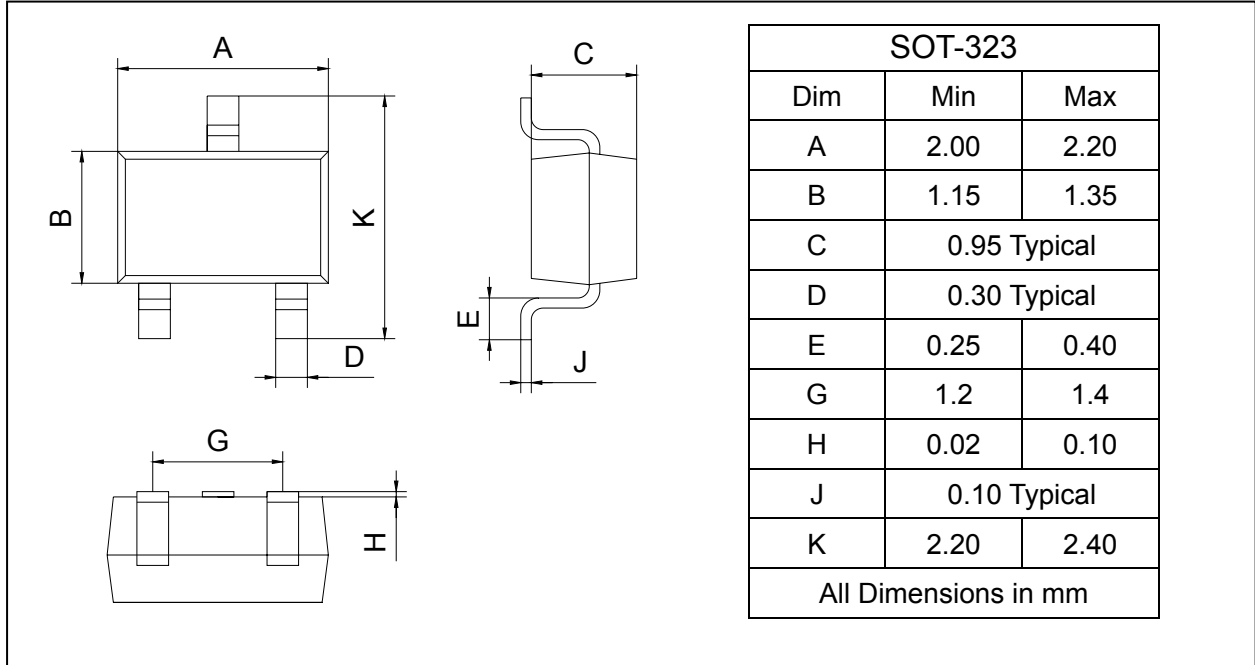
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**KTC4076**

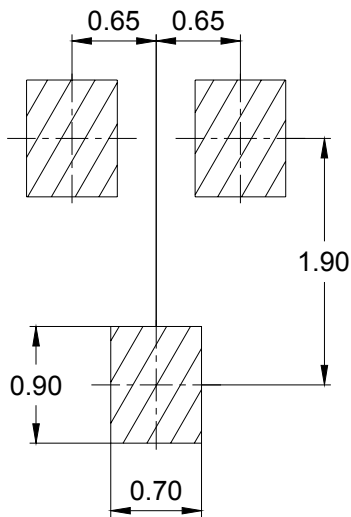
**PACKAGE OUTLINE**

Plastic surface mounted package

SOT-323



**SOLDERING FOOTPRINT**



Unit : mm

**PACKAGE INFORMATION**

Device	Package	Shipping
KTC4076	SOT-323	3000/Tape&Reel